

N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

Rev. 1 — 22 March 2012

**Product data sheet** 

#### 1. Product profile

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#### 1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### **1.3 Applications**

- DC DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>		-	6.27	7.4	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; I_D = 25 \; A; \; T_j = 25 \; ^\circ C; \\ \text{see} \; \underline{Figure \; 6} \end{array}$		-	3.8	4.5	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $V_{DS}$ = 40 V;		-	25	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	125	-	nC
	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C};$ $I_D = 100 \text{ A}; \text{ V}_{sup} \le 80 \text{ V};$ $R_{GS} = 50 \Omega;$ unclamped		-	-	591	mJ

[1] Continuous current is limited by package

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#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

#### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	drain	ii	
				mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

#### 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN4R4-80BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PSMN4R4-80BS	PSMN4R4-80BS

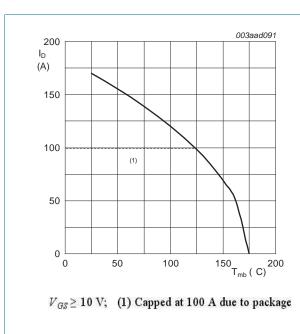
#### 5. Limiting values

#### Table 5. Limiting values

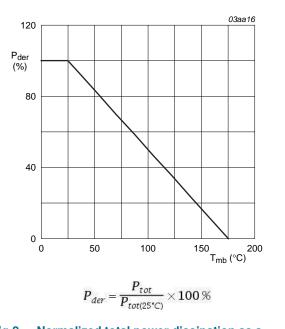
In accordance with the Absolute Maximum Rating System (IEC 60134).

		<b>J</b>				
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>		-	680	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	680	А
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V};  T_{j(init)} = 25 ^{\circ}\text{C};  \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} \leq 80 \text{ V};  \text{R}_{GS} = 50  \Omega; \text{ unclamped} \end{array} $		-	591	mJ
-						

[1] Continuous current is limited by package



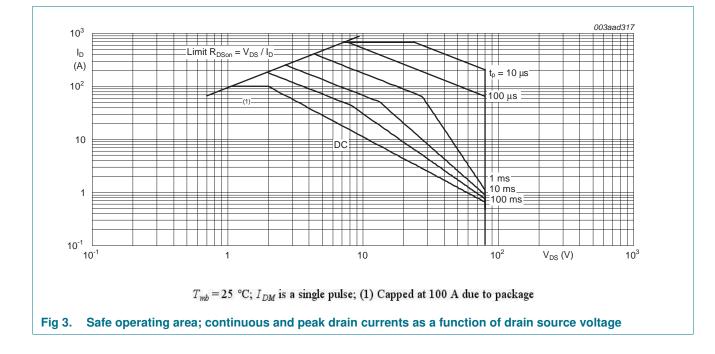
## Fig 1. Normalized continuous drain current as a function of mounting base temperature





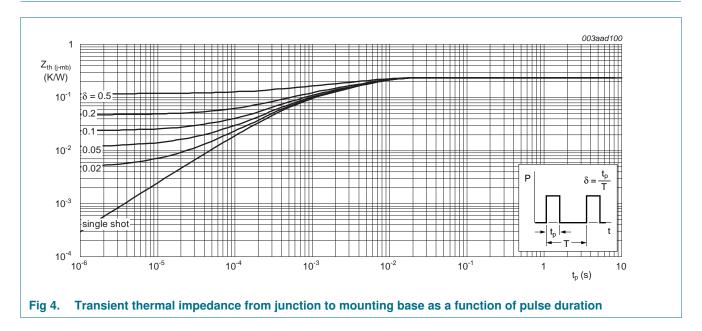
## PSMN4R4-80BS

#### N-channel 80 V, 4.5 m $\Omega$ standard level MOSFET in D2PAK



#### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.23	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



#### 7. Characteristics

#### Table 7. Characteristics

Tested to JEDEC standards where applicable.

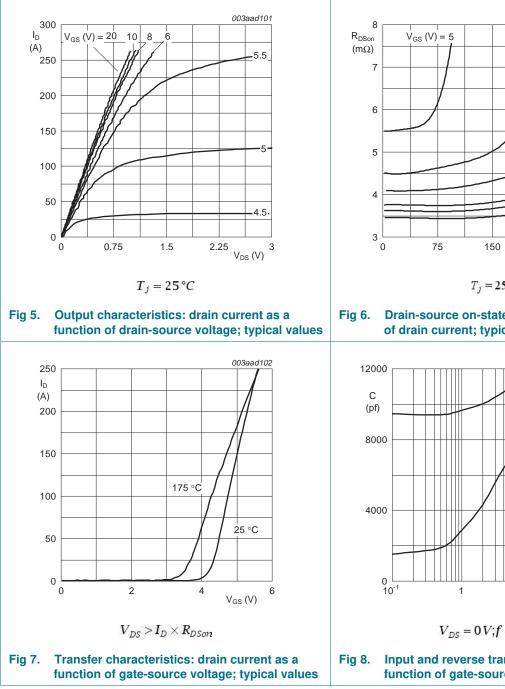
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	73	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>	-	9.12	10.7	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>	-	6.27	7.4	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	3.8	4.5	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	112	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	125	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	39	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	24	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	15	-	nC
Q <sub>GD</sub>	gate-drain charge		-	25	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	4.65	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 V; V_{GS} = 0 V; f = 1 MHz;$	-	8400	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	700	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	336	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.5 \ \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	34.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	38.1	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	66	-	ns
t <sub>f</sub>	fall time		-	18.4	-	ns

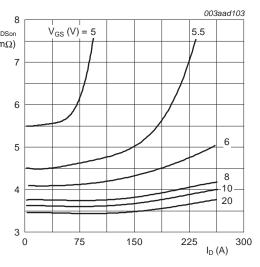
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#### Table 7. Characteristics ... continued

Tested to JEDEC standards where applicable.

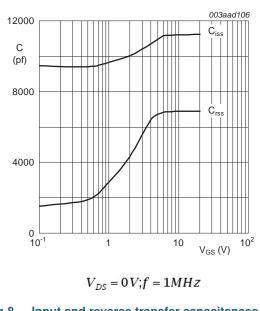
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	59	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	130	-	nC









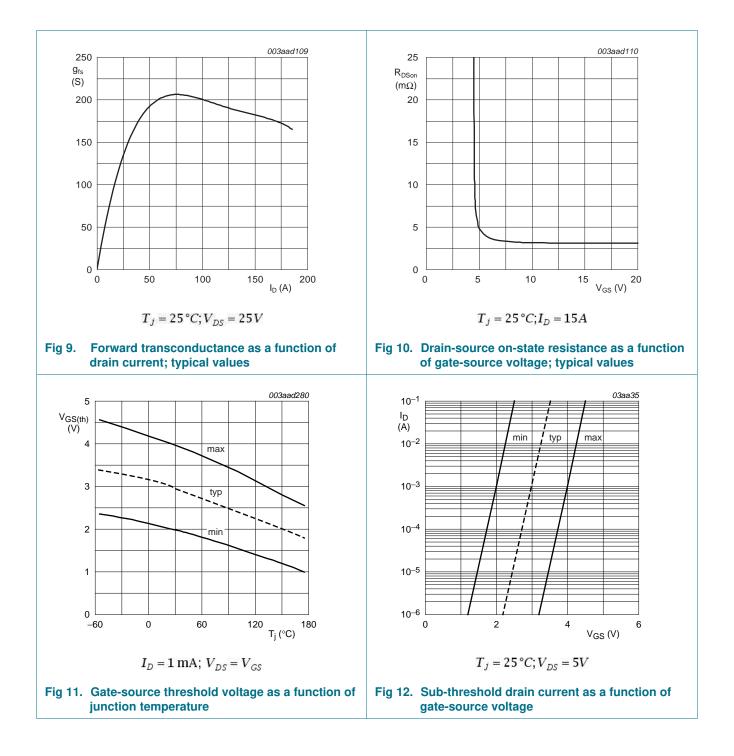




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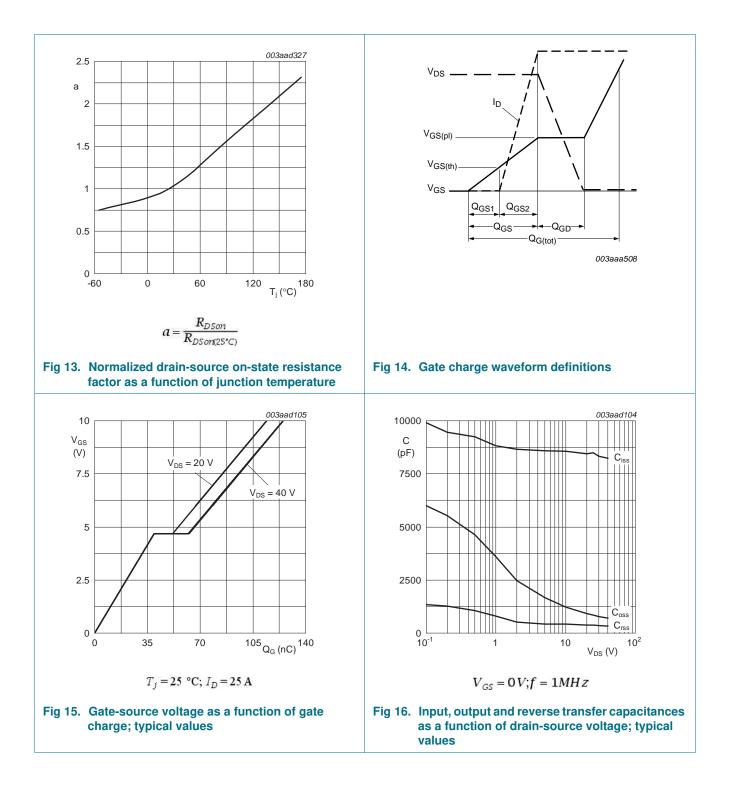
## PSMN4R4-80BS

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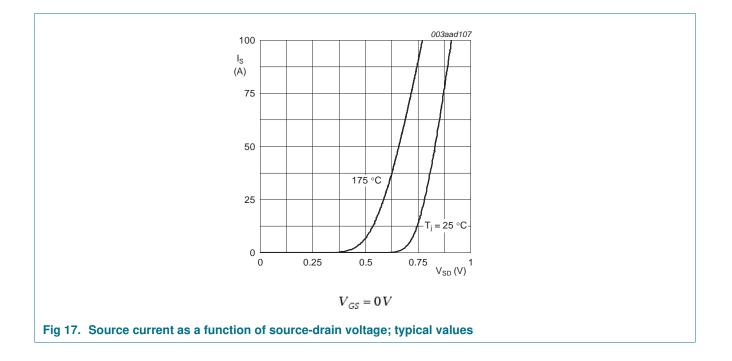
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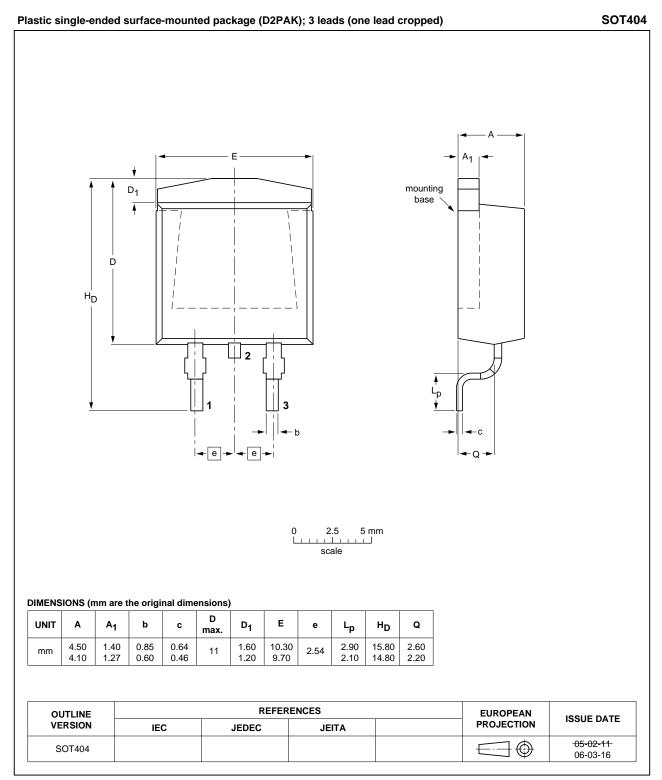
## PSMN4R4-80BS

#### N-channel 80 V, 4.5 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

#### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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#### 9. Revision history

Table 8. Revision	Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PSMN4R4-80BS v.1	20120322	Product data sheet	-	-				

#### **10. Legal information**

#### **10.1 Data sheet status**

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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